NEW PRODUCT

2DD2098R

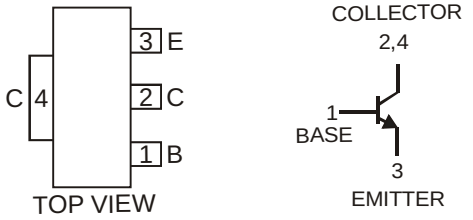
LOW $V_{CE(SAT)}$ NPN SURFACE MOUNT TRANSISTOR

Please click here to visit our online spice models database.

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Resistance $R_{CE(SAT)}$ = 75mΩ at 4A
- Complementary PNP Type Available (2DB1386)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

SOT89-3L



Schematic and Pin Configuration

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	10	A
Continuous Collector Current	I_C	5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T_A = 25°C	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T_A = 25°C	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	—	—	V	I_C = 50μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20	—	—	V	I_C = 1mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	I_E = 50μA, I_C = 0
Collector Cut-Off Current	I_{CBO}	—	—	0.5	μA	V_{CB} = 40V, I_E = 0
Emitter Cut-Off Current	I_{EBO}	—	—	0.5	μA	V_{EB} = 5V, I_C = 0
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.3	1.0	V	I_C = 4A, I_B = 0.1A
DC Current Gain	h_{FE}	180	—	390	—	I_C = 0.5A, V_{CE} = 2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	—	220	—	MHz	V_{CE} = 6V, I_E = -50mA f = 100MHz
Output Capacitance	C_{ob}	—	14	—	pF	V_{CB} = 20V, I_E = 0, f = 1MHz

Notes:
1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

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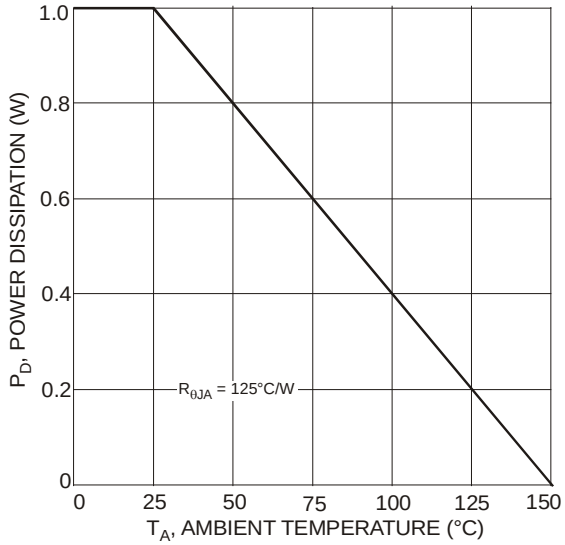


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

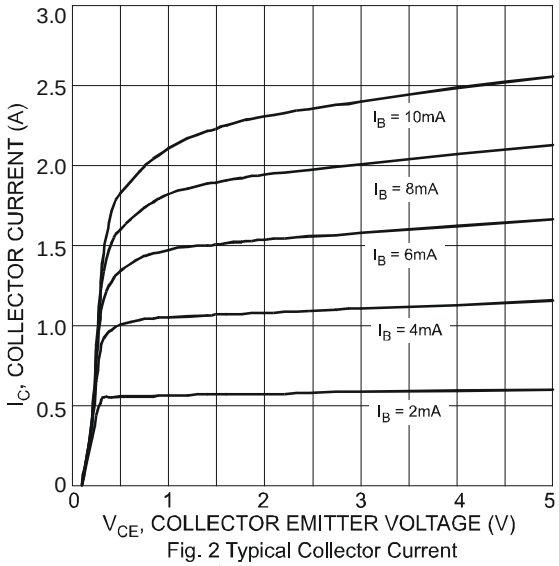


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

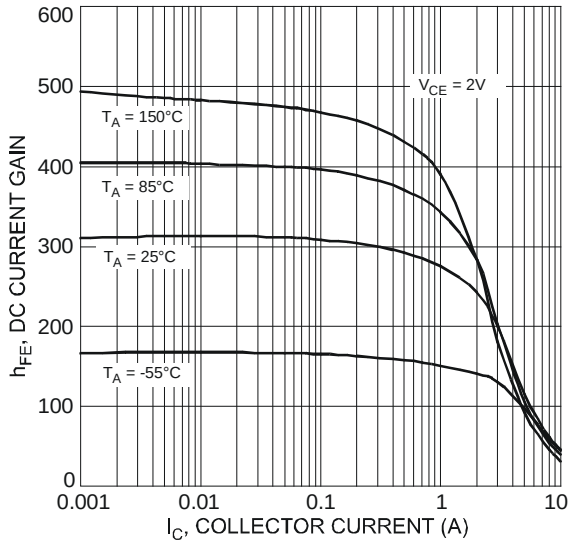


Fig. 3 Typical DC Current Gain vs. Collector Current

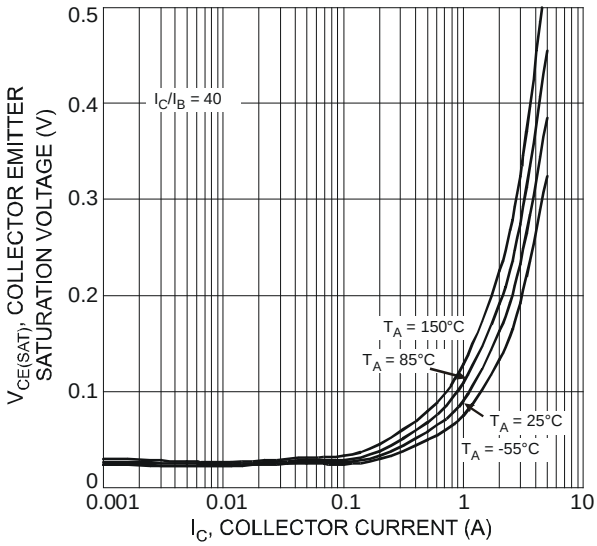


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

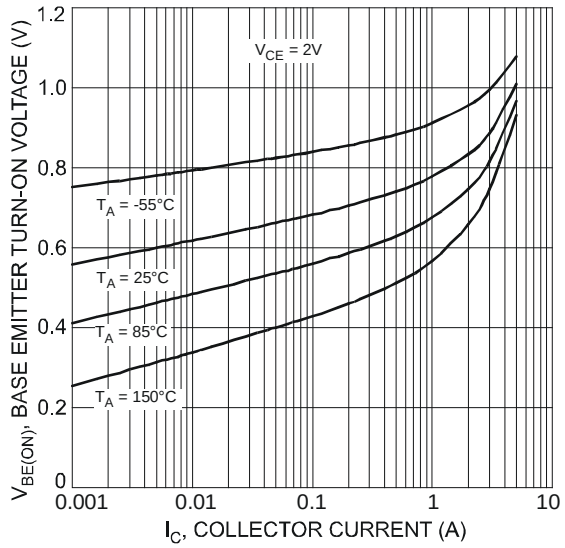


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

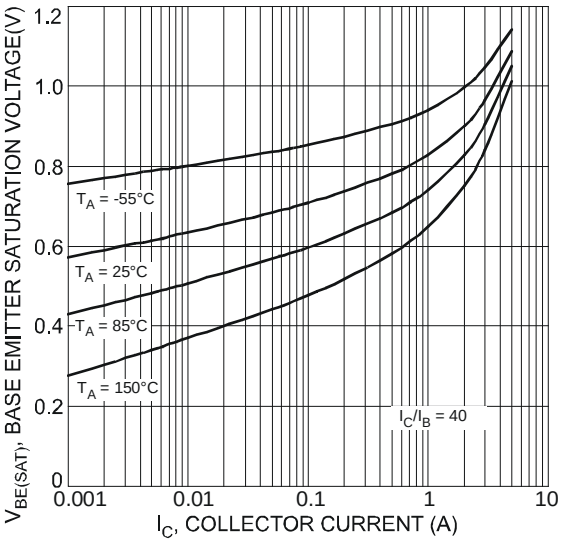


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

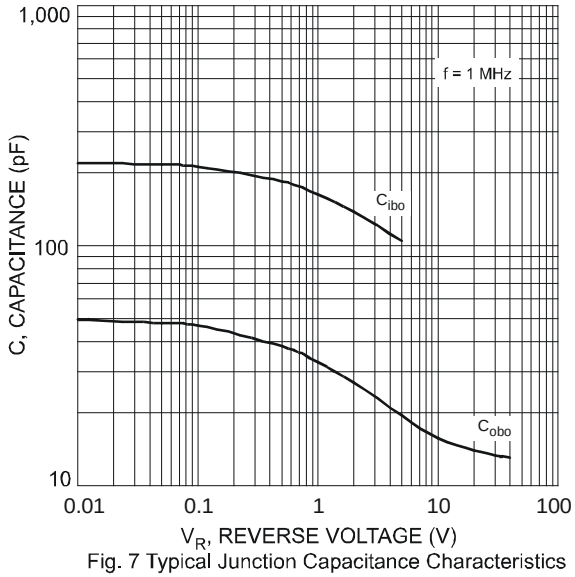


Fig. 7 Typical Junction Capacitance Characteristics

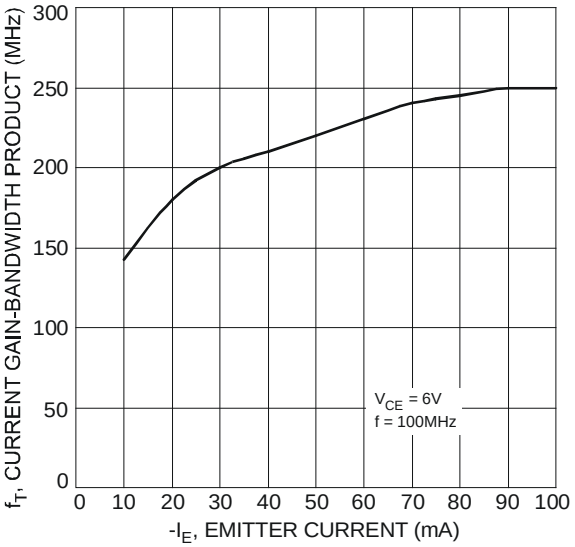


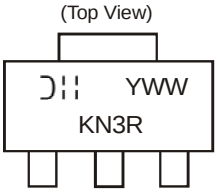
Fig. 8 Typical Gain-Bandwidth Product vs. Emitter Current

Ordering Information (Note 5)

Device	Packaging	Shipping
2DD2098R-13	SOT89-3L	2500/Tape & Reel

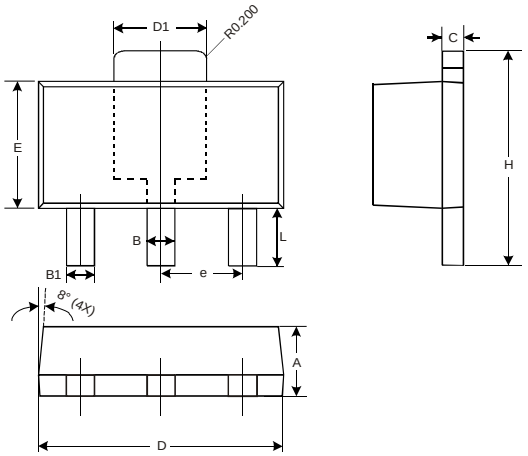
Notes: 5. For packaging details, please see below or go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information



KN3R = Product Type Marking Code
= Manufacturer's Marking Code
YWW = Date Code Marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

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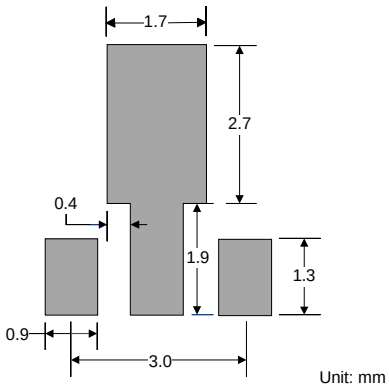
Suggested Pad Layout



Unit: mm